# Theory for Gossam er and Resonating Valence Bond Superconductivity

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We use an elective H am illonian for two-dimensional H ubbard model including an antiferrom agnetic spin-spin coupling term to study recently proposed gossam er superconductivity. We form ulate a renormalized meaneld theory to approximately take into account the strong correlation elect in the partially projected G utzwiller wavefucations. At the half lled, there is a rst order phase transition to separate a M ott insulator at large C oulom b repulsion U from a gossam er superconductor at small U. A way from the half lled, the M ott insulator is evolved into an resonating valence bond state, which is adiabatically connected to the gossam er superconductor.

### 1. Introduction

Since the discovery of high tem perature superconductivity in the cuprates [2, 3], there have been a lot of theoretical e orts trying to understand the microscopic mechanism for it. One of the scenarios was initiated by Anderson [4], who proposed the idea of resonating valence bond (RVB) state for the observed unusual properties in these compounds. A minimum model for cuprates was argued to be 2-dim ensional Hubbard or its equiva-J model in the large U lim it [4, 5]. In the RVB lent t picture, each lattice site is either unoccupied or singly occupied by a spin-up or spin-down electron. The spins are coupled antiferrom agnetically without long range order. The charge carriersm ove in the spin background and condense to a superconducting state [6, 7, 8, 9, 10, 11, 12]. In this scenario, the undoped cuprate with density of one electron per site is a M ott insulator, and the superconductor is viewed as a doped M ott insulator. M any experimentally observed properties in cuprates, such as the d-wave symmetry in superconductivity [13, 14], the pseudogap phenomena [15], and the linear doping dependence of the super uid density in the underdoped region [16], seem to be consistent with the RVB mean eld theory. On the other hand, while mean eld theories and variational calculations show the superconductivity in the doped Hubbard or t J m odels, m ore direct num erical calculations on these m odels rem ain controversial and have been unable to provide unambiguous answers to this question [17, 18, 19, 20, 21, 22].

Very recently, Laughlin has proposed an interesting new notion, the gossam er superconductivity, for high T<sub>c</sub> superconducting Cu-oxides [23]. In a gossam er superconductor, the super uid density is tenuous, in contrast to the conventional superconductor. He proposed an explicit m any body wavefunction for that state, which is a partially G utzw illerprojected BCS state (Eq. (2) below). The partial projection operator enables one to construct its inverse operator. U sing these operators, Laughlin has further proposed a Ham iltonian, for which the partially projected BCS state is an exact ground state. E xact solu-

tions play in portant role in m any physical problem s. By expanding that H am iltonian, Laughlin showed that the superconducting ground state requires a large attractive interaction in addition to a large on-site C oulom b repulsion. This raises the question if the Hubbard or t J m odels capture the basic physics in cuprates.

In a previous paper, one of us argued that the e ective Hamiltonian of the Hubbard model acting on the Gutzwiller's wavefunction should include a spin-spin coupling term, and the on-site C oulom b repulsion plays both the roles in projecting out (partially or completely) the double occupied state and in generating an attractive pairing interaction [24]. A Ithough any variational calculation cannot m ake a conclusion about the exact ground state, it is clear that the spin-spin coupling generated from the Hubbard U should capture some basic features in cuprates including its superconductivity. N evertheless, Laughlin's idea of gossam er superconductivity is interesting. The wavefunction he proposed enables us to study the phase transition between a M ott insulator and a gossam er superconductor at the half lled electron density and to study the strong coupling RVB state from a new view point: namely its adiabatic continuation to the interm ediate coupling gossam er state.

In this paper, we use an e ective H am iltonian (Eq. (1) below) for 2-dimensional Hubbard in square lattice to system atically study the partially projected Gutzwiller wavefunction. We are interested in the competition between the M ott insulator and the superconductor. Here we shall neglect the possible antiferrom agnetism in the model, which will be a subject in a future publication. W e use G utzw iller's approxim ation to replace the strong correlation in the projection by a set of renorm alized factors, and to use a renorm alized m ean eld theory to study the ground state and the elementary excited states of the system . Our main results can be sum marized below . At the half lling, the ground state is a Mott insulator at large U, and a gossam er superconductor at sm all U. The transition is st type in the physically interesting parameter region. The charge carrier density and the superconducting order param eter change discontinuously from zero in the Mott insulating phase to a nite

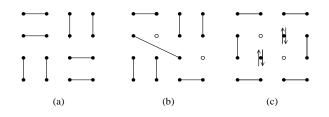


FIG. 1: Snap shots for a) A spin liquid M ott insulator; b). A n RVB superconducting state; and c). A gossam er superconducting state E ach bond connects an up-spin and a dow n-spin and open circle respresents the hole.

value at the critical value of U. Away from the half led, the gossam er superconducting state changes continuously from its state at the half led, while the M ott insulating phase becom es RVB superconducting. The gossam er and RVB suerconducting states have the same pairing symmetry, and their superconducting order parameters are both suppressed by a uni ed renormalized factor, which quantitatively characterizes the sm allness of the super uid density. Therefore, the gossam er and RVB superconducting states are adiabatically connected. The gossam er superconducting state at the half led m ay be viewed as a RVB state with equal number of independent empty and doubly occupied sites. These empty and doubly occupied sites provide "parking space" for singly occupied electrons to move through the lattice. From this point of view, the relative reduction of U respected to the kinetic energy, which m ay be realized by applying the pressure [25], plays a sim ilar role as the chem ical doping. The gossam er superconductivity m ay have already been realized in organic superconductors [26]. In Fig. 1, we schematically show snap shots for a Mott insulator, an RVB state, and a gossam er superconducting state.

This paper is organized as follows. In Section 2, we introduce the model and the variational wavefunction. In Section 3, we formulate a renormalized mean eld theory to study the variational wavefunction. Section 4 is devoted to the phase transition between the M ott insulator and the gossam er superconductor at the half led. D etailed discussions on the gossam er and RVB superconductivity are given in Section 5. The paper is concluded with a summary in Section 6.

### 2. The M odel and the Variational W avefunction

We study an e ective Hubbard Ham iltonian in a square lattice,

$$H = H_{t} + H_{s} + H_{u}$$
(1)  

$$H_{t} = (t_{ij}c_{i}^{y}c_{j} + hc;)$$
  

$$H_{s} = J \qquad \begin{array}{c} < ij > \\ X \\ \\ < ij > \end{array}$$

$$H_{U} = U n_{i''}n_{i\#}$$

In the above equations, ci is the annihilation operator of an electron of spin at the lattice site i, and  $n_i = c_i^{v} c_i$ . The sum is over the nearest neighbor pairs of < ij > , and U > 0 is the intra-site C oulom b repulsion. W ithout loss of generality, we consider the case t > 0. In this H am iltonian, we have introduced an antiferrom agnetic spin-spin coupling term to account for the e ect of the virtual electron hopping process. In the large U lim it, J  $4t^2 = U$ . This model may be viewed as an e ective Ham iltonian of the Hubbard model. The inclusion of the antiferrom agnetic spin coupling appears consistent with the weak coupling renorm alization group analysis [27], and is appropriate in the variational approach studied here. In the limit U ! 1, the model is reduced to the t J model. Very recently, a similar form of the Hamiltonian has been derived by using two subsequent canonical transform ations starting from the Hubbard model at large U lim it [28]. In the Hilbert space with the xed num ber of the doubly occupied electron sites on the lattice, it has been shown that the Hubbard model may be mapped onto Eq. (1) with the constraint that the hopping process in H<sub>t</sub> is limited to the corresponding H ilbert space, namely it does not change the electron double occupation. Here we shall consider Eq.(1) from a phenom enological point of view, and study its solutions within the fram ew ork of G utzw iller's variational approach. W e shall consider J to be an independent param eter.

D ue to the perfect nesting and the van H ove singularity in the density of state, the ground state of H am iltonian (1) at the half lling (electron density n = 1 per site) is an antiferrom agnet for arbitrarily small value of U even in the absence of the spin-spin coupling term. The spin-spin coupling further enhances the magnetism. In this paper, how ever, we shall focus on the insulating and metallic phases of the problem, and will not include the magnetic long range order.

W e study the m odelusing a variational trial wavefunction proposed by Laughlin [23],

$$j_{GS}i = j_{BCS}i$$
(2)

$$= (1 \quad n_{i''} n_{i\#})$$
 (3)

with j<sub>BCS</sub>iaBCS-type superconducting state, given by

$$j_{BCS} = \left[ \begin{array}{c} Y \\ (u_{k} + v_{k} c_{k}^{y} c_{k\#}^{y}) \\ \end{array} \right]$$
(4)

where jDi is the vacuum , and  $\boldsymbol{u}_{k}$  and  $\boldsymbol{v}_{k}$  are variational parameters, satisfying the condition

$$\mathbf{j}_{\mathbf{k}}\mathbf{j} + \mathbf{j}_{\mathbf{k}}\mathbf{j} = 1$$

.

is a projection operator to partially project out the doubly occupied electron states on each lattice site i. The state j<sub>GS</sub> im ay be considered as a generalization of the previously studied partially projected non-interacting electron state [29, 30, 31] to include the superconducting state. In the limiting case  $u_k v_k = 0$ , j<sub>BCS</sub> i is reduced to the non-interacting electron state, and

where j  $_{F L}i$  is the ground state of the non-interacting electron system, given by j  $_{F L}i = \begin{pmatrix} c_{k}^{V} & c_{k} \\ & c_{k} \end{pmatrix}$  ji, with  $_{K}$ ;

the product running over all the  $\tilde{k}$ 's within the Ferm i surface. j<sub>GS</sub> i is a natural generalization of the usual BCS state to strongly correlated system s. It connects the usual BCS state to the RVB state, characterized by the parameter , which takes the value between 0 and 1.

= 0 is a norm alBCS state. At = 1, the projection operator projects out all the doubly occupied electron states, and j<sub>GS</sub> i is reduced to the RVB state [4]. At the half lling and at = 1, each lattice site is occupied by a single electron, and the system is a M ott insulator. Therefore, the wavefunction j<sub>GS</sub> i can be used to study superconductor-insulator transition.

#### 3. The Renorm alized M ean Field Theory

We now proceed the variational calculations to determ ine the parameters and  $u_k$ ,  $v_k$ . W ithout loss of generality, we consider the electron density n 1. The variational energy per site E = hH i is given by

$$E = Ud + hH_{t}i + hH_{J}i$$
 (5)

where  $d = h_{i^{n}} n_{i^{\#}} i$  is the average electron double occupation number. hQ i is the expectation value of the operator Q in the state j  $_{GS}i$ . For briefness, hH  $_{t}i$ ; hH  $_{J}i$ stand for their average values per site. d is a function of , and 0 d 1=4. The rst term in Eq. (5) is the intra-site C oulom b interaction energy, while the second and the third term s are the average kinetic and spin-spin correlation energies, respectively.

The variational calculations can be carried out using variational M onte C arlo m ethod [8, 32, 33, 34]. Here we use the renormalized H am iltonian approach to treat the projection operator approximately [7]. In this approach, the e ect of the projection operator is taken into account by a classical statistical weighting factor, which multiplies the quantum coherent result of the non-projected state. This m ethod (G utzw iller m ethod hereafter) was rst proposed by G utzw iller [30], and has been applied to study strongly correlated systems by m any others [7, 29, 31]. Let hQ i<sub>0</sub> be the expectation value of Q in the state j  $_{BCS}$  i, then the hopping energy and the spin-spin correlation in the state j  $_{GS}$  i are related to those in the state j  $_{BCS}$  i by,

$$hc_i^y c_j i = g_t hc_i^y c_j i_0$$

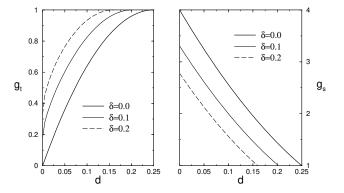


FIG.2: The Gutzwiller's renorm alization factors,  $g_t$  and  $g_s$ , as functions of the double occupation number d, obtained from Eqns. (6). = 1  $n_e$ .

$$hS_{i} S_{j}i = g_{s}hS_{i} S_{j}i_{0}$$
 (6)

The renorm alized factors  $g_t$  and  $g_s$  are determined by the ratio of the probability of the physical processes in the states j  $_{GS}i$  and j  $_{BCS}i$ . Following the counting m ethod described in the literature [7], we have

$$g_{t} = \frac{(n \quad 2d) \left(\frac{p}{d} + \frac{p}{1 \quad n+d}\right)^{2}}{(1 \quad n=2)n}$$

$$g_{s} = \frac{(n \quad 2d)^{2}}{(1 \quad n=2)^{2}n^{2}}$$
(7)

The expression for  $g_t$  is the same as in the early literature [29]. In the limit d = 0, Eqns. (7) recover the previous results derived for the t J model [7]. These renormalized factors quantitatively describe the correlation e ect of the on-site repulsion. g 1, and g << 1 at small d and small , representing the reduction of the kinetic energy due to the projection. 4 g 1, and  $g_s$  = 4 at d = 0 and = 0, representing the enhancement of the spin-spin correlation due to the projection. In Fig2, we plot  $g_t$  and  $g_s$  as functions of the double occupation number d for various electron densities.

In term s of these renorm alization factors, we can de ne a renorm alized H am iltonian given by

$$H^{0} = g_{t}H_{t} + g_{s}H_{s} + H_{U}$$
 (8)

The expectation value of H in the state j  $_{G\,S}i$  can be evaluated in term s of the expectation value of H  $^0$  in the state j  $_{B\,C\,S}i$ . W e obtain,

$$E = hH^{0}i_{0} = Ud + g_{t}hH_{t}i_{0} + g_{s}hH_{J}i_{0}$$
(9)

In the renorm alized H am iltonian approach, the original variational parameters f ; $v_k$ ; $u_k$ g are transformed into the variational parameters fd; $v_k$ ; $u_k$ g. There is one to one correspondence between and d. W ithin the Gutzw iller approximation, one can analytically calculate  $d = hn_{i''}n_{i\#}i$ , and one nds [30, 31],

$$(1 )2 = \frac{d(1 n+d)}{(n=2 d)2} (10)$$

The energy in Eq. (9) is evaluated for the xed number of electrons N<sub>e</sub>. We introduce a Lagrangian multiplier ~, and de ne

$$K = H^{0} \sim (n_{i} N_{e}):$$
 (11)

W e then have E = hK  $i_0$  , being subject to the condition  $0\,hK$   $i_0=0\,\sim$  = 0, or

$$2 v_{k}^{2} = n$$
(12)

Below we consider the case  $u_k$  and  $v_k$  to be real. Evaluating Eq. (11), we obtain (lattice constant = 1),

$$E = U d + \sim + 2^{\Lambda} (g_{t_{\tilde{k}}} \sim) v_{k}^{2} + \frac{X}{V_{\tilde{k}} K^{0}} (v_{k}^{2} v_{k^{0}}^{2} + u_{k} v_{k} u_{k^{0}} v_{k^{0}})$$
(13)

where

$$V_{k} = \frac{3}{2}g_{s}J(\cos k_{x} + \cos k_{y})$$

$$_{k} = 2t(\cos k_{x} + \cos k_{y}) \qquad (14)$$

C arrying out the variational procedure with respect to  $u_{\nu}$  and  $v_{\nu}$  , we obtain

$$u_{R}^{2} = \frac{1}{2} (1 + {}_{R} = E_{R})$$
$$v_{R}^{2} = \frac{1}{2} (1 + {}_{R} = E_{R})$$
(15)

where

$$E_{\kappa} = \frac{q}{\kappa} \frac{2}{\kappa} + \frac{2}{\kappa}$$
(16)

The variational parameters  $_{k}$  and  $_{k}$  are related to the particle particle amplitude  $_{k}$  and the particle hole paring amplitudes  $_{k}$  by,

$$_{\mathfrak{k}} = {}_{x} \operatorname{cosk}_{x} + {}_{y} \operatorname{cosk}_{y}$$

$$_{\mathfrak{k}} = {}_{\widetilde{\mathfrak{k}}} ({}_{x} \operatorname{cosk}_{x} + {}_{y} \operatorname{cosk}_{y}):$$
(17)

In the above equations, we have introduced two correlation functions in the unprojected state  $j_{BCS}i$ ,

$$= \Pr_{P} c_{i^{\#}} c_{i^{+}} ; " \quad Q_{i^{*}} c_{i^{+}} ; \# i_{0}$$
  
=  $hc_{i}^{y} c_{i^{+}} \quad i_{0}$  (18)

with = x; y, the unit vectors on the lattice, and

$$\tilde{k} = [2gt(\cos k_x + \cos k_y) ~ \sim] = (3gJ=4):$$
 (19)

For the d-wave pairing state, which has the lowest energy within this class of states as suggested in the previous studies for the t  $J \mod [7, 9, 10, 36]$ , we have x = y =, and x = y =. and are determined by the coupled gap equations,

$$= \begin{array}{c} X \\ = (\cos k_{x})_{k} = E_{k} \\ = (\cos k_{x})_{k} = E_{k} \end{array}$$
(20)

These gap equations must be solved simultaneously with the hole concentration equation, Eq. (12), which can be rewritten as  $= \sum_{\chi} = E_{\chi}$ , with = 1 g. The variation

with respect to d leads to the equation

$$\frac{\partial E}{\partial d} = U + \frac{\partial g_{t}}{\partial d} h H_{t} \dot{i}_{0} + \frac{\partial g_{s}}{\partial d} h H_{J} \dot{i}_{0} = 0: \quad (21)$$

In terms of and , the energy is given by

$$E = Ud 4ngt (3gJ=4)(^{2} + ^{2})$$
 (22)

where and are the solutions of the gap equations, and both are functions of d. In the case there are multiple solutions for d from Eq. (21), the ground state is determ ined by the global energy m inim um. A Iternatively, we m ay solve the gap equations for given values of d, and calculate E (d) to nd the optim al value of d to determ ine the ground state and the ground state energy. The chem icalpotential of the system, = @E = @n, is given by

$$= \sim + \frac{\partial g_{t}}{\partial n} h H_{t} \dot{i}_{0} + \frac{\partial g_{s}}{\partial n} h H_{J} \dot{i}_{0}$$
(23)

Note that chemical potential here is dimensioner from the Lagrangian multiplier ~ in the renormalized mean eld theory. This is because the renormalized factors  $g_t$ ,  $g_s$  to be also functions of electron density n.

## 4. M ott Insulator-G ossam er Superconductor T ransition

In this section, we discuss the variational solutions at the half lkd case. At the half lling, the trial wave-function  $j_{GS}i$  describes either a M ott insulator if = 1 (i.e. d = 0), or a superconducting state if < 1 (i.e. d > 0). If is close to 1, or d is very close to zero,  $j_{GS}i$  describes a gossam er superconducting state.

W e expect a M ott insulator at large U and a superconducting state at sm all U. This can be exam ined qualitatively without carrying out the quantitative calculations. At the half lling,  $q = 8 (1 \quad 2d)d$ , and  $q = 4 (1 \quad 2d)^2$ . Eq. (21) becomes

$$U + 8(1 \quad 4d)hH_ti_0 \quad 16(1 \quad 2d)hH_Ji_0 = 0:$$
 (24)

Since both  $hH_{t}i_{0}$  and  $hH_{J}i_{0}$  are nite, there will be no solution of Eq. (24) if U is su ciently large. This indicates that the ground state corresponds either d = 0 or  $d = d_{max}$ , the allowed maximum value of d. The repulsive nature of U excludes the latter, and it follows that the M ott insulating state with d = 0 is the ground state. W e believe that the qualitative result for the existence of the M ott insulating phase at large but nite U is robust. Note that in the Gutzwiller's wavefunction, the doubly occupied site and the empty site are not correlated. At the half lling, d represents the carrier density n and is proportional to the D rude weight in the a.c. conductivity, n  $e^2 = m$ , with m the e ective mass. We remark that the param eter d in our G utzw iller approach is different from the usual double occupation number  $\tilde{\alpha}$  (for example, the double occupation calculated in the exact diagonalization of a nite size system). In the latter case, d also includes the contribution from the virtual hopping process. Therefore, the double occupied site is bound to the empty site, and the double occupation number d'does not represent the mobile carriers.

In the insulating phase, the ground state is the same as that of the Heisenberg m odel. W ithin our theory, the ground state energy is given by

(

$$E_0 = 3J({}^2_0 + {}^2_0)$$
 (25)

$$p_{0} = 0 = C = \frac{p}{2}$$
$$= \frac{1}{p} \frac{X}{8} q \frac{q}{\cos^{2} k_{x} + \cos^{2} k_{y}} = 0.339; (26)$$

At small U, one expects a metallic ground state, except in the special cases due to the band e ect, such as having the Von Hove singularity and perfect nesting in  $H_t$ . In this paper, we will not consider the special band e ect. Therefore, we expect a metal-insulator transition at a

nite  $U = U_c$  in the general case, with the m etallic phase to be superconducting provided that  $u_k v_k \in 0$ . This is the M ott insulator-gossam er superconductor transition.

We now discuss the phase transition in details. We solve the gap equations for the xed d and determ ine the transition point  $U_c$  and the nature of the transition. The phase diagram in the parameter space U and J=t is plotted in Fig. 3. The critical  $U_c$  separates the M ott insulating phase from the gossam er superconducting phase. We can choose the mobile carrier density as the order parameter, which is proportional to d. The phase transition is classified as the second type if d! 0 and the rst type if d!  $d_c > 0$  as U!  $U_c$  within the metallic phase. This classified is consistent with the usual zero temperature quantum phase transition, where the nature of the phase transition depends on the continuity or discontinuity of the order parameter. We nd the transition to be the rst order at 0 < J=t < c, and the second order

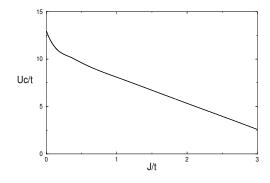


FIG.3: Phase diagram at the half lling.

at  $_{\rm c} < J=t$ , with  $_{\rm c}$  2. At J = 0, the present theory is reduced to the Brinkm an-Rice theory form etal-insulator transition [29] for the projected non-interacting electron state. In that case, we nd U<sub>c</sub>=t= 128= <sup>2</sup>. From Fig. 3, we see that U<sub>c</sub> (J ! 0) = U<sub>c</sub> (J = 0), so that the critical value of U is continuous at J = 0. However, the transition is the second type at J = 0, while it is the rst type for any sm all but nite J=t.

Let us rst discuss the rst order phase transition in the region 0 < J=t < 2. In Fig. 4, we show the energy E as a function of d for several values of U at a typical parameter J=t = 1=3. E is not a monotonic function of d for U near U<sub>c</sub>. As d increases from d = 0, Eincreases linearly, then decreases, then increases again. There is a local energy m in imum around d = 0.02, which develops and becomes a globalm in im um as U approaches  $U_c$  from the insulator side. The local minimum E (d<sub>c</sub>) at  $d = d_c$  represents a m etallic solution, and E (d = 0) represents an insulator solution. The critical value for the M ott insulator and gossam er superconductor transition is determined by the condition  $E(d_c) = E(d = 0)$ . From Fig. 4, we have  $U_c = t = 10.23$  for J = t = 1 = 3. At  $U > U_c$ , d = 0, and the ground state is an insulator. At  $U < U_{c}$ , 0:02, and the ground state is a gossam er superd d. conducting state. In Fig. 5, we plot d as a function of U.d is approximately linear in U till the transition point U<sub>c</sub>. The discontinuity in d is about 0.02. We conclude that the M ott insulator-gossam er superconductor phase transition in this most relevant region is st type. The carrier density is discontinuous at the phase transition point. Since d is proportional to the carrier density, this type of st order transition should be observable in the electric transport or in the a.c. conductivity measurements.

For large ratio of J=t, our calculations show that the phase transition is second order. This is illustrated in Fig. 6 for E v.s. d in the case of J=t = 3. The transition occurs at  $U_c = 2.58t$ , and d changes continuously across  $U_c$ .

A special case is J = 0. In this limit,  $j_{GS}i =$ 

j  $_{\rm F\,L}$  i, and our theory is reduced to the previous one for the projected Ferm i liquid state. The energy in Eq.

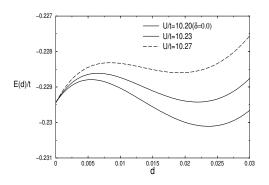


FIG. 4: The energy E as a function of d for U around the critical value  $U_c$  at = 0. The ratio J=t=1=3.

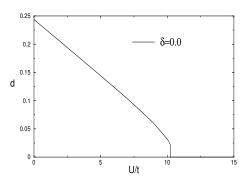


FIG.5: The double occupation number d as a function of U at = 0 and J=t=1/3.

(9) at the half lling becomes  

$$E = U d 2g j cosk_{x} + cosk_{y} j$$

$$= U d 128d (1 2d) t=^{2}$$
(27)

From this we nd  $U_c$ =t = 128= <sup>2</sup> 13. d is continuous at  $U_c$  so that the transition is second type.

Our result on the storder phase transition in the physically interesting region (sm all but non-zero J=t) is somewhat unexpected. We argue that the storder

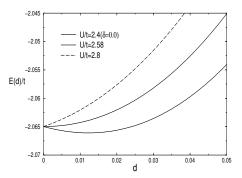


FIG.6: The energy E as a function of the double occupation number d for several values of U around the critical value  $U_c$  with = 0 and J=t= 3.

transition between the M ott insulator and the gossam er superconductor is due to the interplay of the kinetic and spin-spin correlation energies. This interplay was not included in the previous study of the G utzw iller approach but is taken into account here. To illustrate the e ect of the interplay to the nature of the phase transition, we consider the limiting case 0 < J=t < < 1, and expand the energy E of Eq. (22) at n = 1 for sm all d,

$$E(d) = E_0 + (U U_{c0})d d^2 + O(d^3)$$
 (28)

where  $E_0$  is the energy at d = 0 given by Eq. (25),  $U_{c0} =$  $16^{16}$  2Ct  $12C^{2}J$  is the solution of 0E = 0d = 0 at d = 0, given by Eq. (24). =  $[32(0 = 0d)_{\dot{h}_{0}}]$ 32 2C) t. The J-dependence in has been neglected since J=t << 1. Note that the kinetic energy is proportional to .-pAs dincreases from 0, tends to increases from  $_0 = C = 2$  to gain more kinetic energy. Therefore, @ =@d > 0. In the  $\lim \pm J = t < < 1$ , we have  $\emptyset = \emptyset d = ($  $_{0})=d/t=J>>1,$ hence the st term in the expression for dominates > 0. This demonstrates that d = 0 is a local and maximum in energy at  $U = U_{c0}$ , and the phase transition occurs at a large value of U corresponding to d > 0 as num erically shown in Fig. 4, hence it is a rst order transition. Numerically, we not that = 34:8472, for J=t=1=3.

It is interesting to compare the gossam er superconductor -M ott insulator transition with the metal-insulator transition studied in previous literature [29]. In the Brinkman-Rice theory, the transition is second order. In that theory, the system approaches the insulating phase, the elective mass m ! 1. In the gossam er superconductor-M ott insulator transition with small ratio of J=t, the insulating phase is not characterized by the divergence of the elective mass. We estimate the ratio of the elective mass to the band mass (1/t) at the metallic side of transition point to be 1=g<sub>t</sub> 1=(8d) 6.

The rst order phase transition between metal and insulator was rst pointed out by Peierls [37] and by Landau and Zeldovich [38], and exam ined in m ore great detail by M ott [39]. In their theory, an electron is always bound to a positive charge due to the long range C oulom b attraction, and the transition of a metal to an insulator at zero or very low tem peratures occurs at a nite critical electron density, and must be rst type. It is interesting to note that the on-site repulsion also leads to the rst order transition between a speci c type of metal (superconductor) and an insulator studied in the present paper, where the long range C oulom b force is not included. W e also note that Florencio and Chao [40] investigated the m etal-insulator transition of the H ubbard m odelusing Gutzwiller's wavefunction by including antiferrom agnetism and found the transition to be rst type.

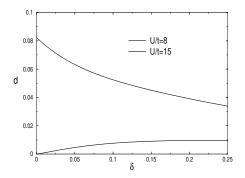


FIG. 7: The double occupation number d as a function of at the ratio J=t=1=3 for several U's.

## 5. Gossam er and RVB superconductivity

In this section, we discuss the superconducting state at the half lkd as well as away from the half lkd. Note that at > 0,  $j_{GS}$  i always describes a metallic state. To make the term inology clearly, we shall call the superconducting state at U < U<sub>c</sub> to be the gossam er superconductor [23, 24], and the doped M ott insulator (U > U<sub>c</sub> and > 0) to be the RVB state [4].

W e begin with the discussion of the double occupation number d as a function of the hole concentration. We solve the gap equations and nd the optim al value of d. The results are plotted in Fig. 7. We nd that d is always non-zero at > 0, even in the region  $U > U_c$ . This suggests that the doped M ott insulator is described by a partially projected state ( < 1 in Eq. (2)). Nevertheless, d is very sm all for U U<sub>c</sub>. As we can see from Fig. 7, d varies from 0 to 0:01 for U=t=15, which corresponds to  $U=U_{c}$ 1:5. The non-zero value of d at > 0 m ay be understood from the variational equation (21), which determ ines d. At > 0,  $Q_{q}=Qd_{h_{e_0}} ! 1$ . Therefore, d = 0 cannot be a solution of the equation, and d must be nite. It remains to be seen if this result is due to the G utzw iller's approxim ation used in our calculation. It will be interesting to further exam ine this issue using other m ethods such as the variational M onte Carlomethod.

From Fig. 7, we also see that as increases from 0, d increases for large U while d decreases for small U. The latter may be understood as follows. In the small U case, the correlation becomes less important, and the qualitative feature between d and becomes similar to the uncorrelated state. For the uncorrelated Fermi liquid state,  $d = (1 \quad j=4$ , so that d monotonically decreases as increases.

W hile d is a smooth function of for most values of U in our study, there is a narrow region in U above  $U_c$ , d changes discontinuously at a very small . In Fig. 8, we show the energy E v.s. d for U = 10.235t, slightly above  $U_c = 10.23t$ , for four values of . At = 0, d = 0

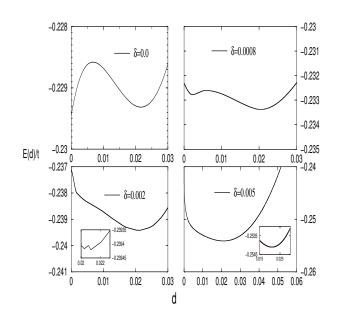


FIG .8: Energy E as a function of d for U =  $10\,235t^{\,>}$  U  $_{c}$  at the ratio J=t = 1=3, for several values of  $\,$  .

corresponds to the global energy m inimum, while there is a local m inimum around d = 0.02. As gradually increases, the positions of the two m inim a change sm oothly and their corresponding energies reverse their order. In this region, the optimal value of d jumps. This region is found very narrow: 10.23t < U < 10.235t, how ever.

W e now discuss the superconducting order param eter. The superconducting order param eter of the state j  $_{G\,S}$  i is de ned by, for the d-wave pairing,

$$s_{c}() = h_{\underline{i}\#} c_{\underline{i}+} \ "i \ h_{\underline{i}"} c_{\underline{i}+} \ \#i;$$
 (29)

and  $_{sc} = _{sc}(x) = _{sc}(y)$ . We shall adopt the Gutzwiller approximation to calculate this quantity. In analogy to the derivation for the hopping energy in Eq.(6), we not that [7]

$$< c_{i\#}c_{i+} = g_t < c_{i\#}c_{i+} > 0$$
 (30)

Therefore the order parameter  $_{sc}$  is related to the variational parameter in the gap equations by

$$_{\rm sc} = g_{\rm t}$$
 (31)

In Fig. 9, we show our results for  $_{sc}$  and as functions of for three values of U: well above  $U_c$ , at  $U_c$ , and well below  $U_c$ . Note that at  $U = 15t >> U_c$ ,  $_{sc} = 0$  at = 0, although takes a maximum. This is consistent with the M ott insulating ground state. At increases, the kinetic energy plays m ore important role in comparison with the spin-spin correlation energy, and decreases m onotopically. However,  $_{sc}$  shows a non-m onotonic dome shape, and it is increases to reach a peak before it drops for larger U. A lso note that at  $U_c$  the M ott

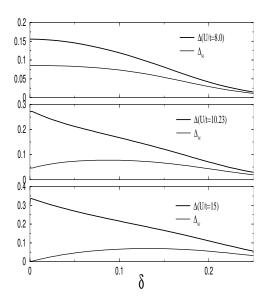


FIG.9: Variational parameter and superconducting order parameter  $_{sc}$  as functions of the hole concentration for three values of U at ratio J=t= 1/3.

insulator and gossam er superconducting state are degenerate at = 0, and the gossam er superconducting phase continuously evolves into the metallic phase at > 0. Shown in the gure for U = 10.23t U is the metallic phase. The non-zero value of  $_{sc}$  at = 0 indicates the transition to be the rst order.

In Fig. 10, we show  $_{sc}$  and as a function of U for = 0. From this gure we can see that for U < U,  $_{sc}$  and both increase with U.At U  $U_c$  takes a maximum while  $_{sc} = 0$ . Note that at small values of U, the e ective H am iltonian does not represent the original H ubbard m odel, and one should be cautious to interpret the results at small U.

It is interesting to point out that the superconducting order parameter  $~_{\rm sc}$  in both the gossam er and RVB superconducting states are characterized by the variational param eter and a sm all renorm alized factor gt. They have the same pairing symmetry, and the two states are adiabatically connected to each other. From this point of view, the gossam er and RVB superconductors are the same. In Fig. 11, we present a schematical diagram for the M ott insulator, gossam er and RVB superconducting states. In the parameter space of C oulom b repulsion U and of the hole concentration , there is a line at = 0and at U >  $U_c$  for the M ott insulating phase. In the region  $U > U_c$  and > 0, it is the RVB superconducting phase as Anderson proposed [4]. In the region  $U < U_{c}$ , it is the gossam er superconducting phase in which both the half led and non-half led states are superconducting.

W hile the gossam er and RVB superconducting states are essentially the same, the chemical potential in the gossam er superconducting state is continuous at = 0

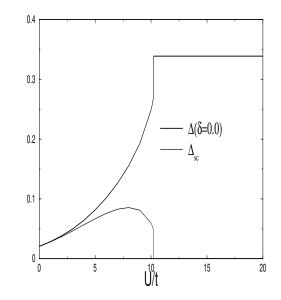


FIG.10:Variationalparameter and superconducting order parameter  $_{sc}$  as functions of U at = 0 and J=t = 1=3.

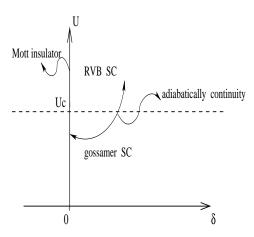


FIG.11: Schem atical phase diagram for the H am iltonian in parameter space U and  $% \mathcal{A}$  .

because of the m etallic phase, while is discontinuous at = 0 because the state at = 0 is an insulator and the state at any smallbut nite is a m etal within the present theory.

Below we shall study quantitatively. At = 0, = U=2 by electron-hole sym metry. At other value of , we calculate using Eq. (23) after solving the gap equations. In Fig. 12, we show as a function of . As we can see = U=2 at = 0, and is continuous from the gure, for U  $U_c = 10.23t$ . There is a discontinuity in for  $U > U_c$  at = 0. At  $U > U_c$ , the chem ical potential is shifted from U=2 at the half led to the lower Hubbard band away from the half lled. To see this more explicitly, wede ne = (d!0) (d = 0). as a function of U is plotted in Fig. 13. As U decreases, decreases m onotonically and reaches a nite value at  $U = U_c + 0^+$ ,

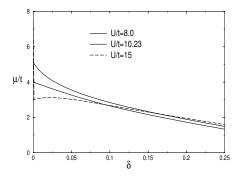


FIG.12: The chemical potential as a function of the hole concentration for several values of intra-site C oulom b repulsion U with J=t=1=3.

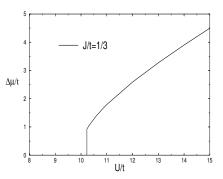


FIG. 13: The discontinuous in the chem ical potential as a function of intra-site C oulom b repulsion U for J=t=1/3.

then drops to zero at  $U = U_c$  O. The discontinuity of at  $U_c$  is related to the storder phase transition.

Finally, we brie y discuss the excited states. In the context of the G utzw iller trial wavefunction, the excited states were discussed by Zhang et al. [7] for the RVB state, and recently by Laughlin for a gossam er superconductor H am iltonian [23]. Following Zhang et al., the quasiparticle states can be de ned by

$$j_{p"}i = c_{p"}^{Y} (u_{\tilde{k}} + v_{\tilde{k}} c_{\tilde{k}}^{Y} c_{\tilde{k}\#}^{Y}) j0i \qquad (32)$$

The quasiparticle energy  $E_p$  is defined to be the difference of the expectation values of K in Eq. (32) in this state and in the ground state j  $_{GS}$  i. We use the Gutzw iller method to calculate the energy and obtain [7]

$$E_{p} = (3g_s J=4) \frac{2}{p} + \frac{2}{p};$$
 (33)

At the vectors p satisfying  $_{p} = 0$  (Eq. (17)), we have  $E'_{p} = j\cos k_{x} \cos k_{y}$  j. Therefore, the quasipartical energy is proportional to the parameter , and not renormalized by the factor  $g_{t}$ , which is very dimensional to the superconducting order parameter. From Fig. 9, our theory predicts the quasipartical energy to be maximum at = 0, and decreases as doping increases. This

## 6. Sum m ary

We have used the Gutzwiller variational method to study an elective H am iltonian for 2-dimension Hubbard modelB ased on Gutzwiller approximation, we have discussed the case both at the half lled and away from the half lled. At the half lled, there is a rst order phase transition to separate a Mott insulator at large Coulomb repulsion U from a gossamer superconductor at small U.T his is very interesting. It suggests that the on-site Coulomb repulsion can lead to the rst transition between a speci c type of metal and an insulator. The double occupation number d which is proportional to the carrier density changes discontinuously from zero in the Mott insulator phase to a nite value at the phase transition point (U = U<sub>c</sub>). So we expect that this type of

rst order transition should be observable in the electric transport or in the a.c. conductivity m easurem ents. Away from the half lled, the Gutzwiller variational state is always metallic. The gossam er superconducting state changes continuously from its state at the half led, while the M ott insulating phase becom es RVB superconducting. The gossam er superconductor is sim ilar to the RVB suerconducting states with the same paring sym metry, and showing the pseudogap. Their major di erence is on the position of their chem ical potential. The Gutzwiller method we used in this paper has previously been tested in good agreem ent with variational M onte Carlo method [7, 8]. We believe that the qualitative conclusions obtained here should be reliable, and re ned num erical calculations such as variational M onte C arlo calculations will be interesting to exam ine the problem .

There are other questions that require further investigation such as the e ect of the antiferrom agnetism which is most plausible in this model.

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